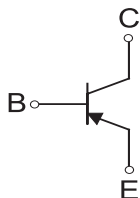
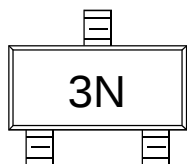


SOT-523 Plastic-Encapsulate Transistors**MMBT3906T**

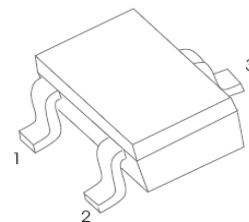
TRANSISTOR (PNP)

FEATURES

- Complementary To MMBT3904T(NPN)

MARKING**Equivalent Circuit**

HFE	100-300	
RANK	L	H
RANGE	100 - 200	200 - 300

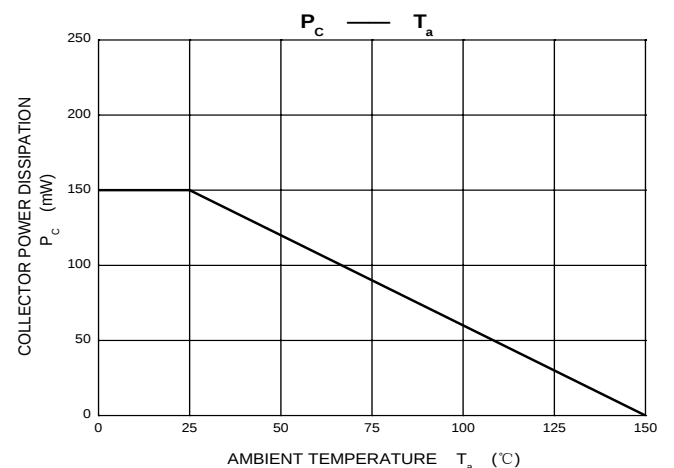
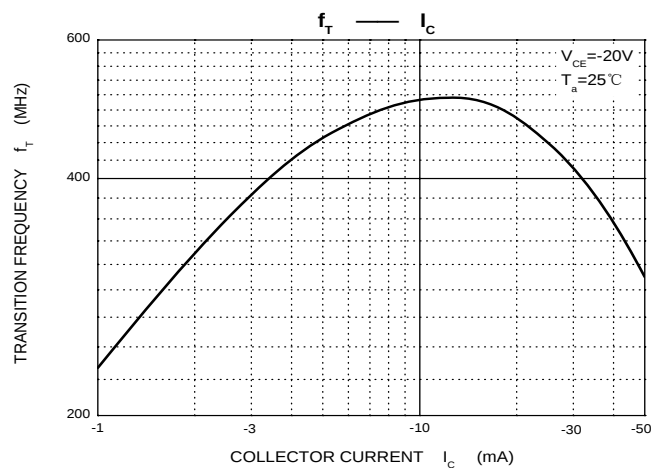
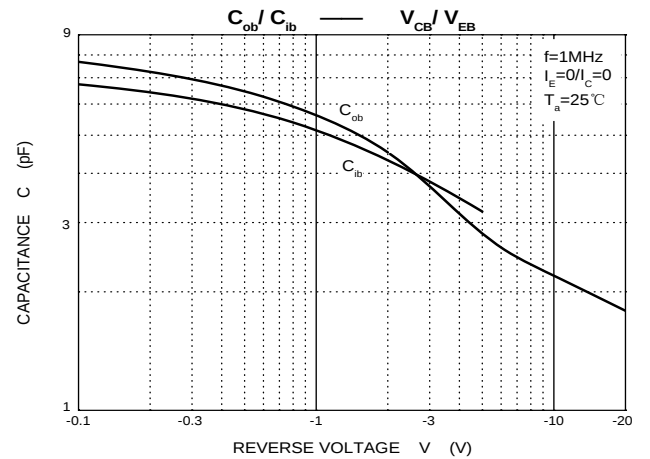
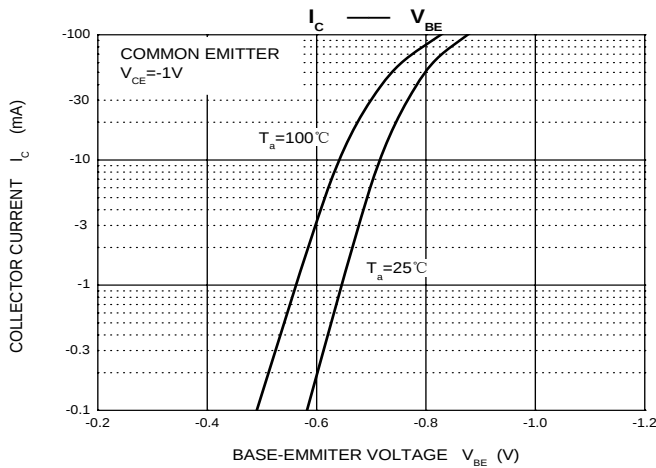
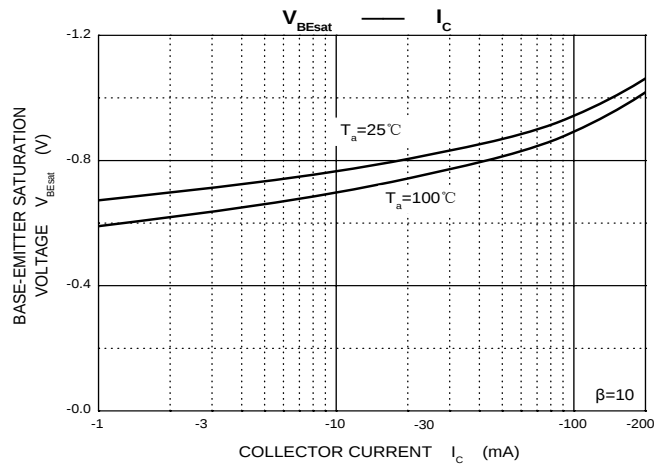
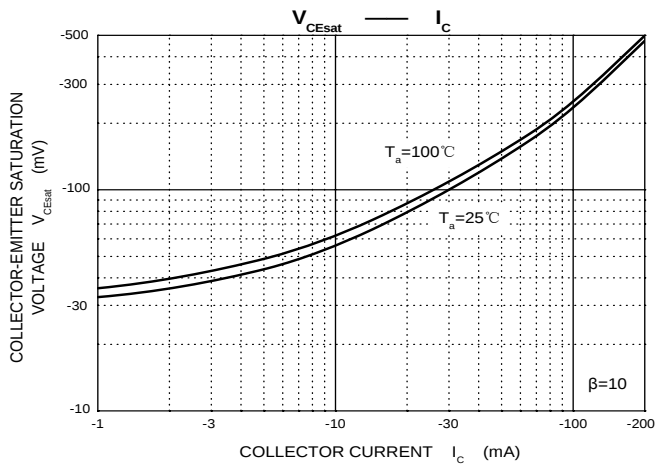
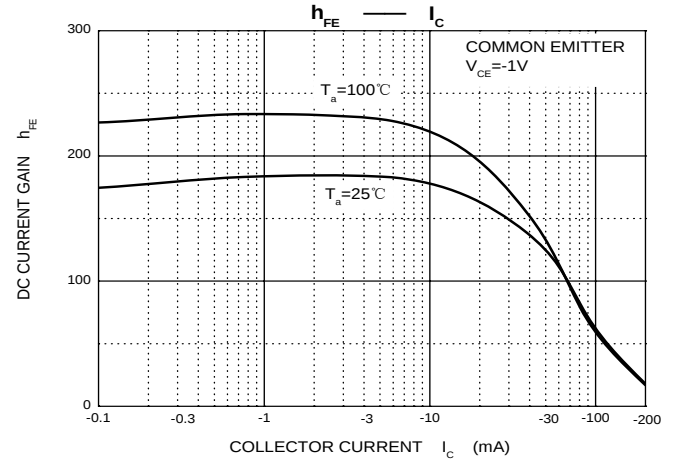
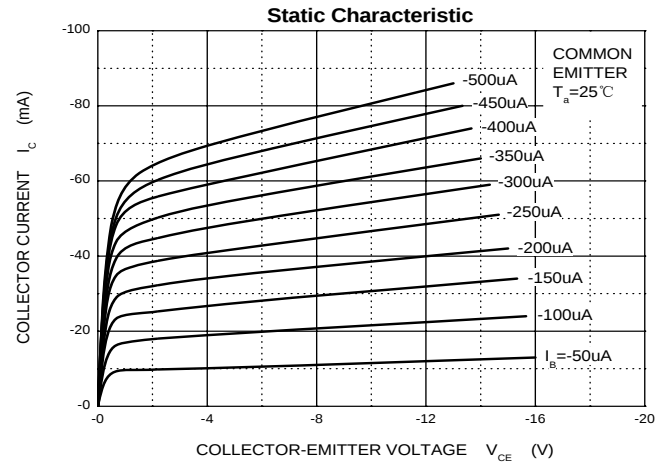
SOT - 523**1. BASE****2. EMITTER****3. COLLECTOR****MAXIMUM RATINGS** ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current -Continuous	-200	mA
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	833	$^{\circ}\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}\text{C}$

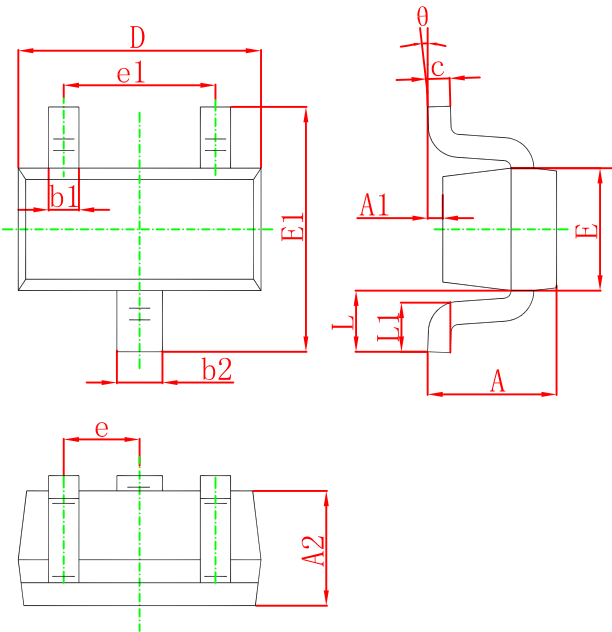
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
Collector cut-off current	I_{CEX}	$V_{CB}=-30\text{V}, V_{BE(off)}=-3\text{V}$			-0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-0.1\text{mA}$	60			
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	80			
	$h_{FE(3)}$	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=-2\text{V}, I_C=-100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.25	V
	$V_{CE(sat)2}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$	-0.65		-0.85	V
	$V_{BE(sat)2}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.95	V
Transition frequency	f_T	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	250			MHz
Collector output capacitance	C_{obo}	$V_{CB}=-5\text{V}, I_E=0, f=1\text{MHz}$			4.5	pF
Input capacitance	C_{iob}	$V_{EB}=-0.5\text{V}, I_E=0, f=1\text{MHz}$			10	pF
Noise figure	NF	$V_{CE}=-5\text{V}, I_C=0.1\text{mA}$			4	dB
Delay time	t_d	f_{Ω} $V_{CC}=-3\text{V}, V_{BE(OFF)}=-0.5\text{V}$			35	nS
Rise time	t_r	$I_C=-10\text{mA}, I_{B1}=-1\text{mA}$			35	nS
Storage time	t_s	$V_{CC}=-3\text{V}, I_C=-10\text{mA}$			225	nS
Fall time	t_f	$I_{B1}=I_{B2}=-1\text{mA}$			75	nS

Typical Characteristics

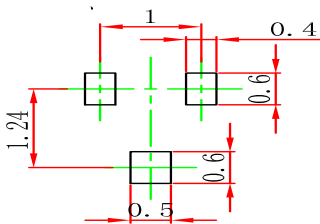


Package Outline Dimensions (SOT-523)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout (SOT-523)



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.